## Description

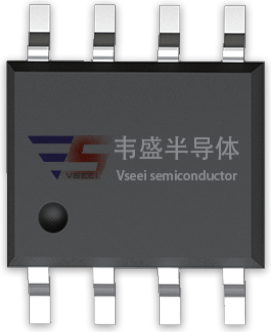
The VSM11N03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.It is ESD protested.

## General Features

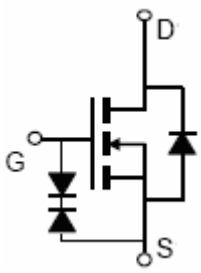
- $V_{DS}$ = 30V,$I_D$ =11A
  $R_{DS(ON)}$ < 10mΩ @ $V_{GS}$=10V
  $R_{DS(ON)}$ < 14mΩ @ $V_{GS}$=4.5V
  ESD Rating: 2000V HBM
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

## Application

- PWM application
- Load switch




SOP-8




Schematic Diagram

## Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| VSM11N03-S8 | VSM11N03 | SOP-8 | Ø330mm | 12mm | 2500 units |

## Absolute Maximum Ratings ($T_A$=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 30 | V |
| Gate-Source Voltage | $V_{GS}$ | ±10 | V |
| Drain Current-Continuous | $I_D$ | 11 | A |
| Drain Current-Pulsed (Note 1) | $I_{DM}$ | 50 | A |
| Maximum Power Dissipation | $P_D$ | 2.5 | W |
| Operating Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 To 150 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Resistance,Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 50 | ℃/W |

## Electrical Characteristics ($T_A$=25℃unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 30 | | - | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=30V,$V_{GS}$=0V | - | - | 1 | μA |
| **Parameter** | **Symbol** | **Condition** | **Min** | **Typ** | **Max** | **Unit** |
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±10V,$V_{DS}$=0V | - | - | ±10 | μA |
| **On Characteristics** (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 1.0 | 1.5 | 2.0 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=8A | - | 7 | 10 | mΩ |
| | | $V_{GS}$=4.5V, $I_D$=6A | - | 10 | 14 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=10V,$I_D$=11A | 25 | - | - | S |
| **Dynamic Characteristics** (Note4) | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=15V,$V_{GS}$=0V, F=1.0MHz | - | 1155 | - | PF |
| Output Capacitance | $C_{oss}$ | | - | 260 | - | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 95 | - | PF |
| **Switching Characteristics** (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=15V,$R_L$=2.2Ω $V_{GS}$=5V,$R_{GEN}$=3Ω | - | 10 | | nS |
| Turn-on Rise Time | $t_r$ | | - | 16 | | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 40 | | nS |
| Turn-Off Fall Time | $t_f$ | | - | 10.8 | | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=15V,$I_D$=8A, $V_{GS}$=4.5V | - | 17.5 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 4.5 | - | nC |
| Gate-Drain Charge | $Q_{gd}$ | | - | 2.5 | - | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage (Note 3) | $V_{SD}$ | $V_{GS}$=0V,$I_S$=1A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | $I_S$ | | - | - | 11 | A |

Notes:

**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
**2.** Surface Mounted on FR4 Board, t ≤ 10 sec.
**3.** Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
**4.** Guaranteed by design, not subject to production

## Typical Electrical and Thermal Characteristics

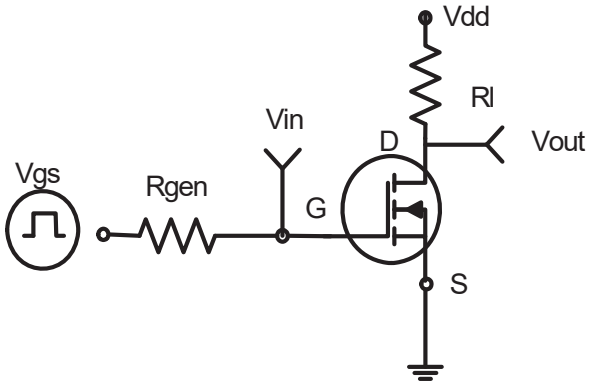



**Figure 1:Switching Test Circuit**

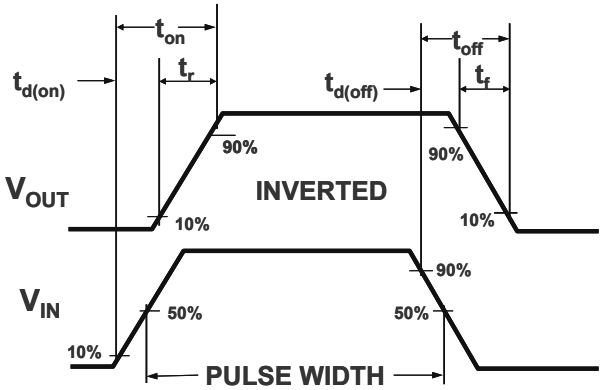
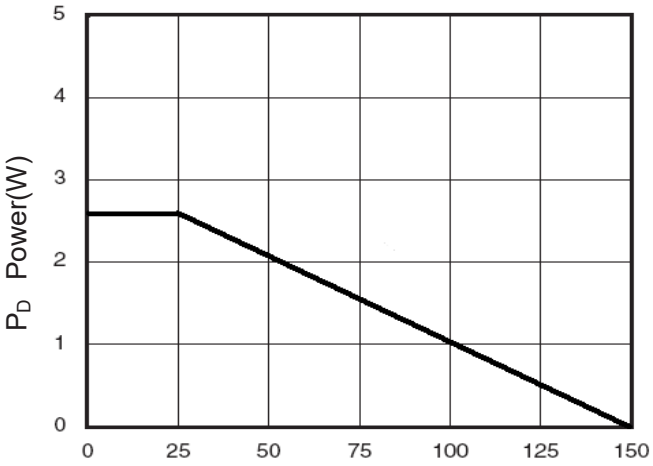
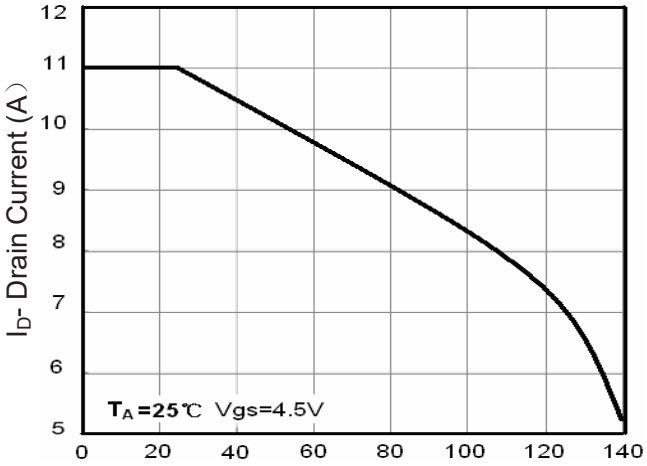



**Figure 2:Switching Waveforms**



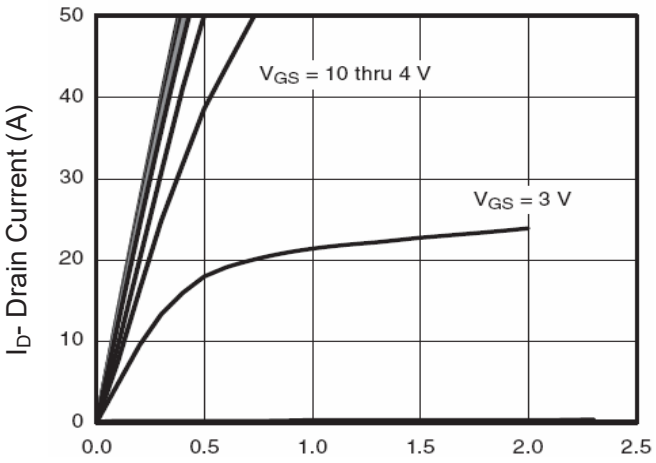

TJ-Junction Temperature(℃)

**Figure 3 Power Dissipation**



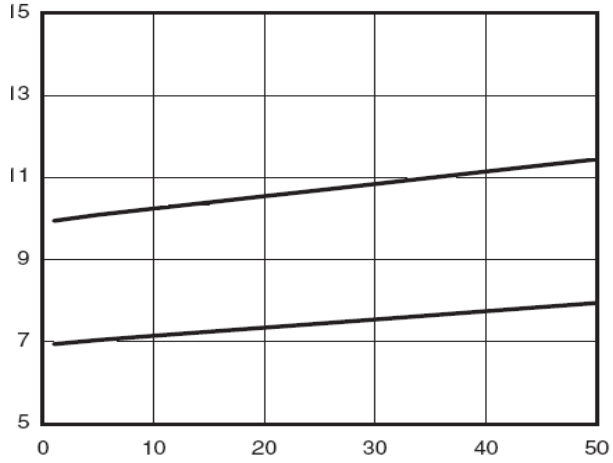

TJ-Junction Temperature(℃)

**Figure 4 Drain Current**




Vds Drain-Source Voltage (V)

**Figure 5 Output Characteristics**




ID Drain Current (A)

**Figure 6 Drain-Source On-Resistance**

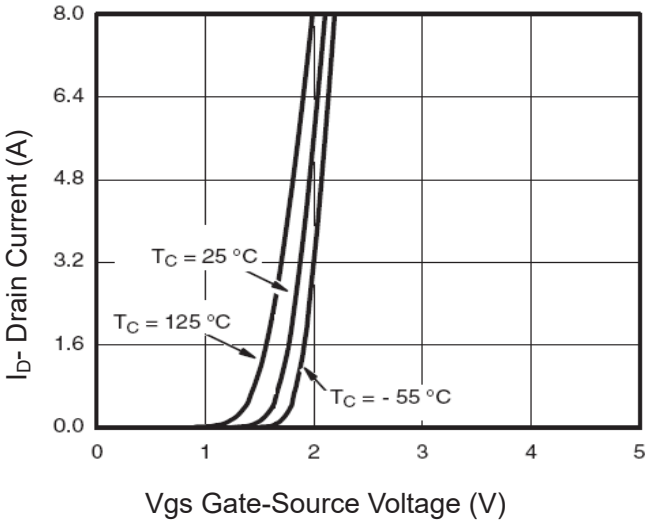



**Figure 7 Transfer Characteristics**

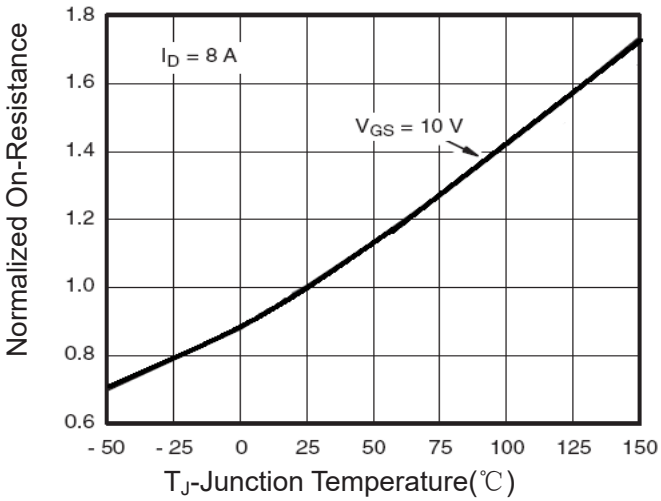



**Figure 8 Drain-Source On-Resistance**

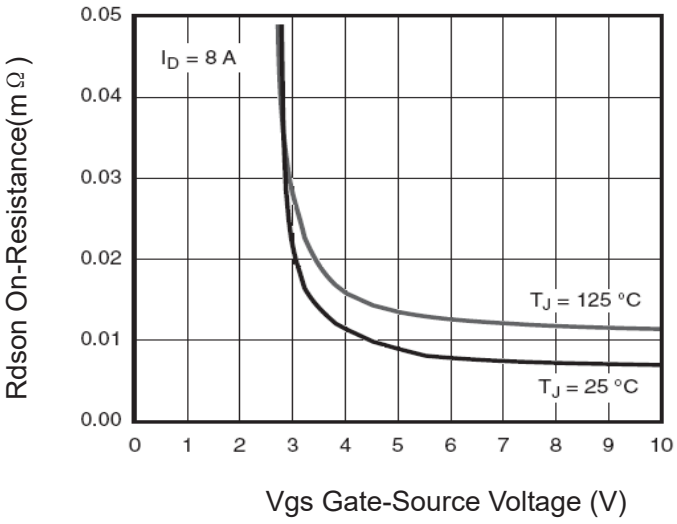



**Figure 9 Rdson vs Vgs**

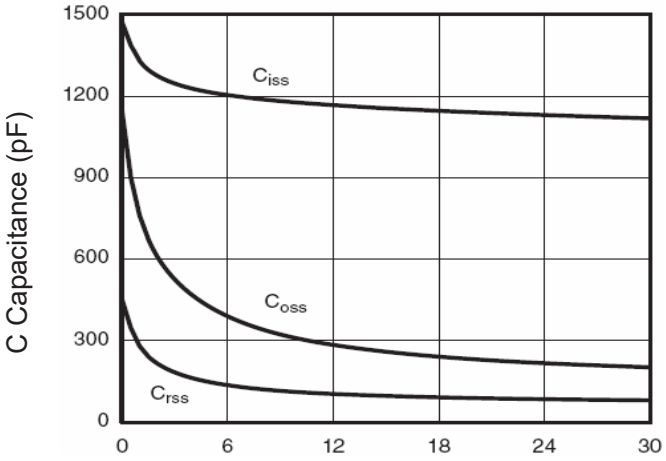



**Figure 10 Capacitance vs Vds**

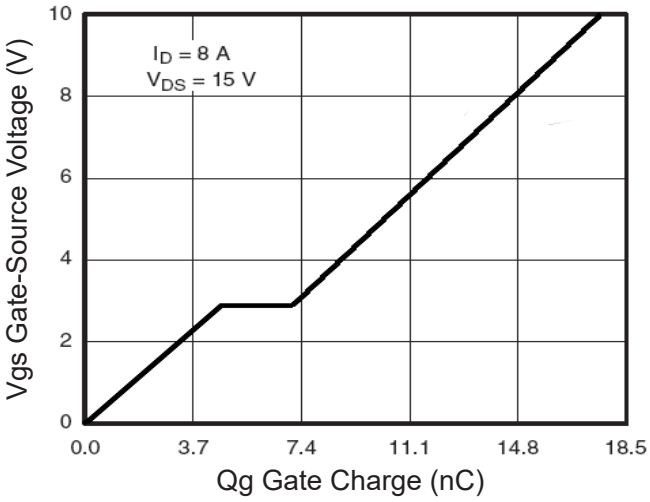



**Figure 11 Gate Charge**

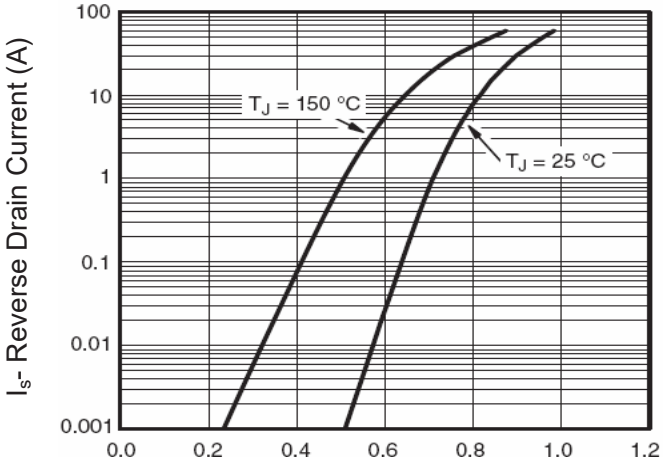



**Figure 12 Source- Drain Diode Forward**

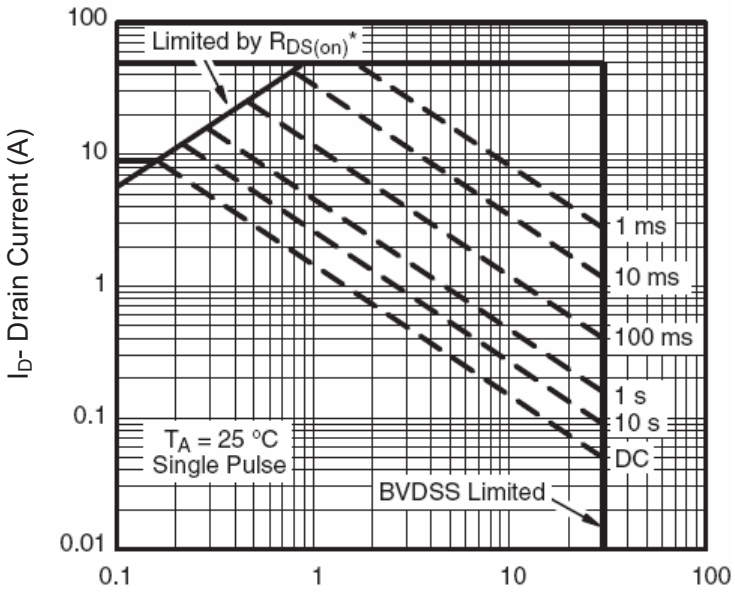



**Figure 13 Safe Operation Area**

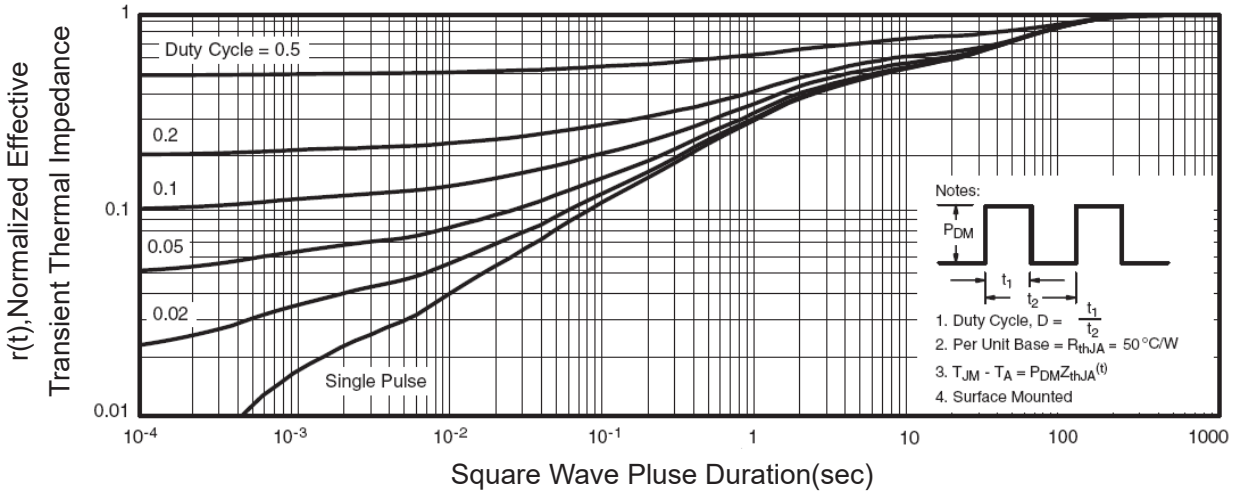



**Figure 14 Normalized Maximum Transient Thermal Impedance**